SiHU6N80E-VB Datasheet

N-Channel 800V (D-S) Super Junction Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V) at T_J max.	800	
$R_{DS(on)}$ typ. (Ω) at 25 °C	V_{GS} = 10 V	0.850

FEATURES

- Low figure-of-merit (FOM) R_{on} x Q_g
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)

RoHS COMPLIANT
HALOGEN FREE

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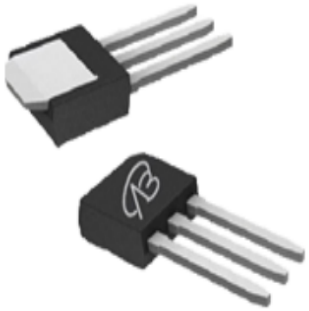
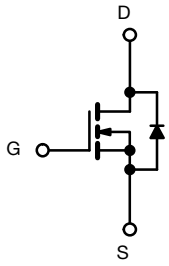




N-Channel MOSFET

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial
  - Welding
  - Induction heating
  - Motor drives
  - Battery chargers
  - Renewable energy
  - Solar (PV inverters)

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V_{DS}	800	V
Gate-source voltage			V_{GS}	± 30	
Continuous drain current (T_J = 150 °C)	V_{GS} at 10 V	T_C = 25 °C	I_D	6	A
		T_C = 100 °C		4	
Pulsed drain current [a]			I_{DM}	18	
Linear derating factor				1.7	W/°C
Single pulse avalanche energy [b]			E_{AS}	580	mJ
Maximum power dissipation			P_D	210	W
Operating junction and storage temperature range			T_J, T_{stg}	-55 to +150	°C
Drain-source voltage slope	T_J = 125 °C		dV/dt	50	V/ns
Reverse diode dV/dt [d]				5.1	
Soldering recommendations (peak temperature) [c]	For 10 s			260	°C

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature
b. V_{DD} = 100 V, starting T_J = 25 °C, L = 30 mH, R_g = 25 Ω, I_{AS} = 8.0 A
c. 1.6 mm from case
d. $I_{SD} \leq I_D$, dI/dt = 100 A/μs, starting T_J = 25 °C

THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum junction-to-ambient	R_{thJA}	-	62	°C/W
Maximum junction-to-case (drain)	R_{thJC}	-	0.65	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	800	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA	-	1.08	-	V/°C
Gate-source threshold Voltage (N)	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2.0	-	4.0	V
Gate-source leakage	I_{GSS}	V_{GS} = ± 20 V	-	-	± 100	nA
		V_{GS} = ± 30 V	-	-	± 1	µA
Zero gate voltage drain current	I_{DSS}	V_{DS} = 800 V, V_{GS} = 0 V	-	-	1	µA
		V_{DS} = 640 V, V_{GS} = 0 V, T_J = 125 °C	-	-	10	
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D =2 A	-	0.850	-	Ω
Forward transconductance	g_{fs}	V_{DS} = 30 V, I_D = 2 A	-	8.7	-	S
Dynamic						
Input capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 100 V, f = 1 MHz	-	2600	-	pF
Output capacitance	C_{oss}		-	81	-	
Reverse transfer capacitance	C_{rss}		-	9	-	
Effective output capacitance, energy related [a]	$C_{o(er)}$	V_{DS} = 0 V to 480 V, V_{GS} = 0 V	-	58	-	
Effective output capacitance, time related [b]	$C_{o(tr)}$		-	296	-	
Total gate charge	Q_g	V_{GS} = 10 V; I_D = 6 A, V_{DS} = 480 V	-	61	122	nC
Gate-source charge	Q_{gs}		-	16	-	
Gate-drain charge	Q_{gd}		-	20	-	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 480 V, I_D = 6 A, V_{GS} = 10 V, R_g = 9.1 Ω	-	22	44	ns
Rise time	t_r		-	24	48	
Turn-off delay time	$t_{d(off)}$		-	71	142	
Fall time	t_f		-	26	52	
Gate input resistance	R_g	f = 1 MHz, open drain	0.3	0.7	1.4	Ω
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	6	A
Pulsed diode forward current	I_{SM}		-	-	12	
Diode forward voltage	V_{SD}	T_J = 25 °C, I_S = 6 A, V_{GS} = 0 V	-	-	1.2	V
Reverse recovery time	t_{rr}	T_J = 25 °C, I_F = I_S = 6 A, dI/dt = 100 A/µs, V_R = 25 V	-	416	832	ns
Reverse recovery charge	Q_{rr}		-	6.4	12.8	µC
Reverse recovery current	I_{RRM}		-	27	-	A

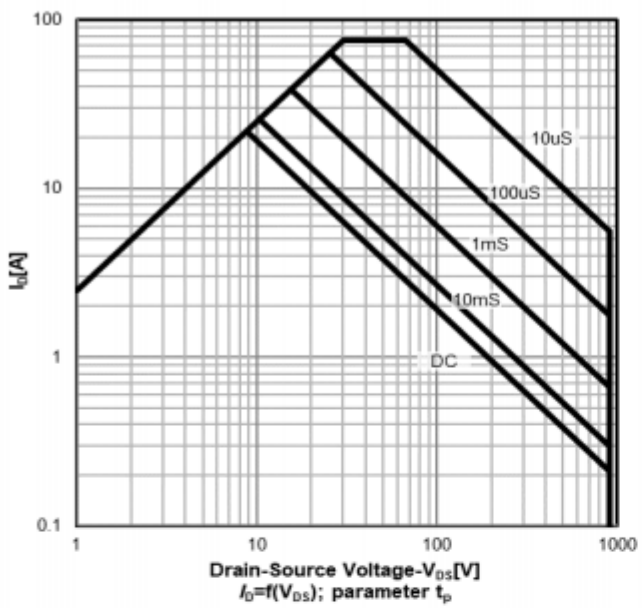
Notes

a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

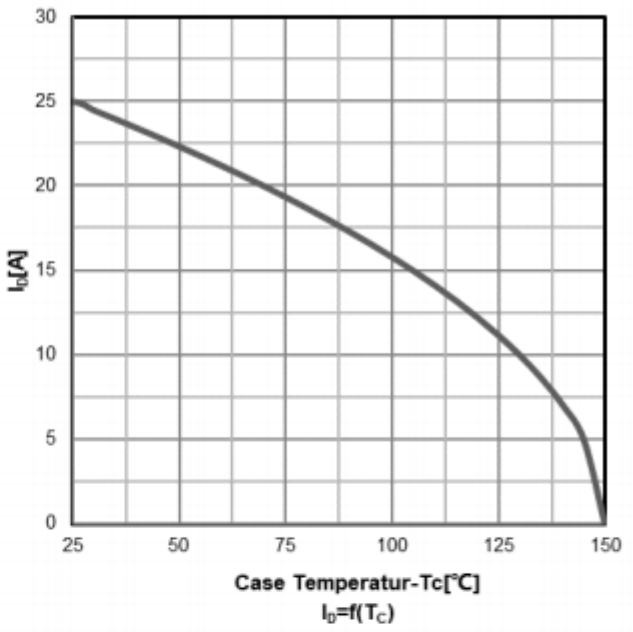
b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

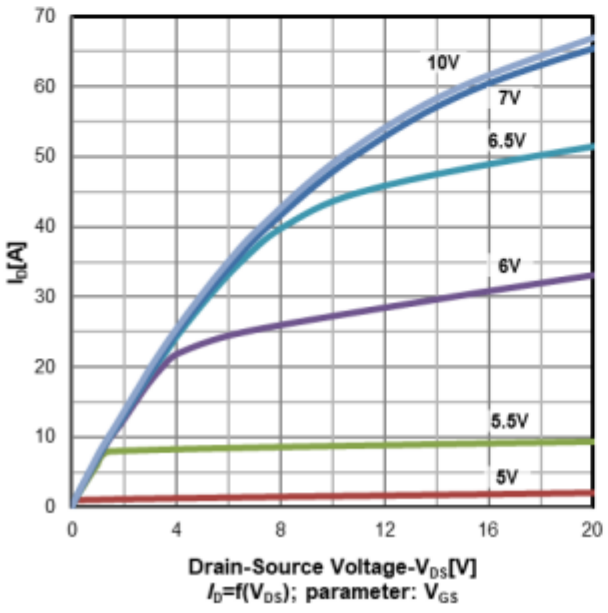
Safe operating area TC=25 ℃
Non FullPAK



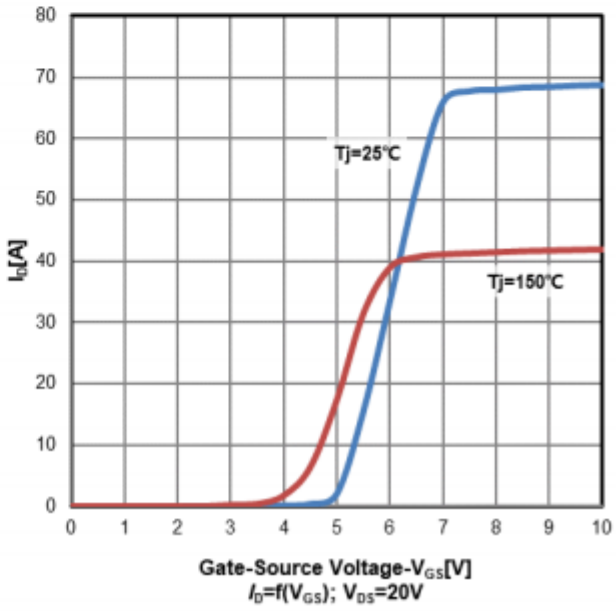
Drain current vs temperature



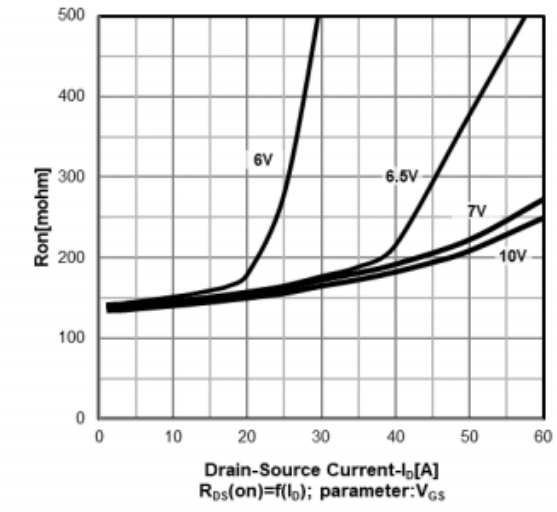
Typ. output characteristics T_j=25 ℃



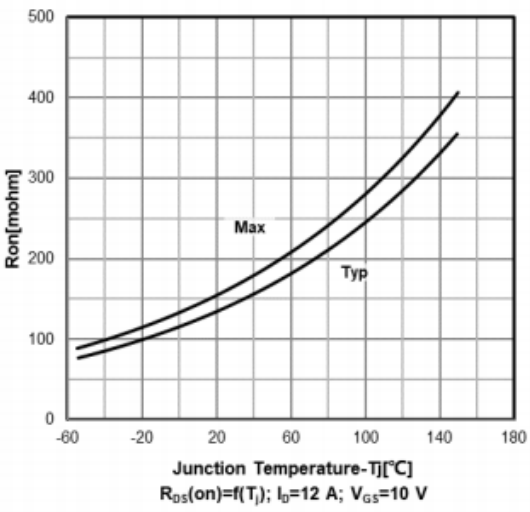
Typ. transfer characteristics



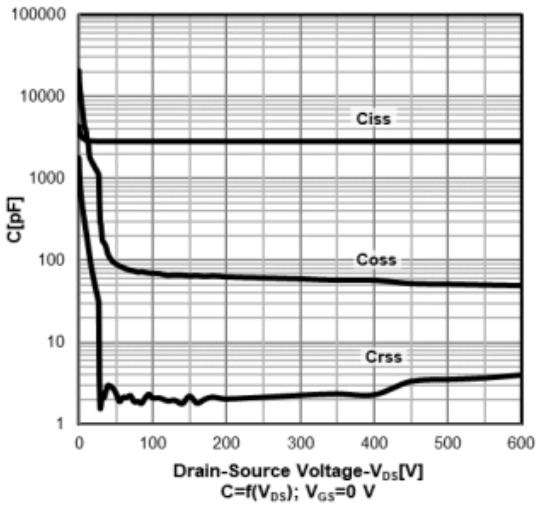
Typ. drain-source on-state resistance



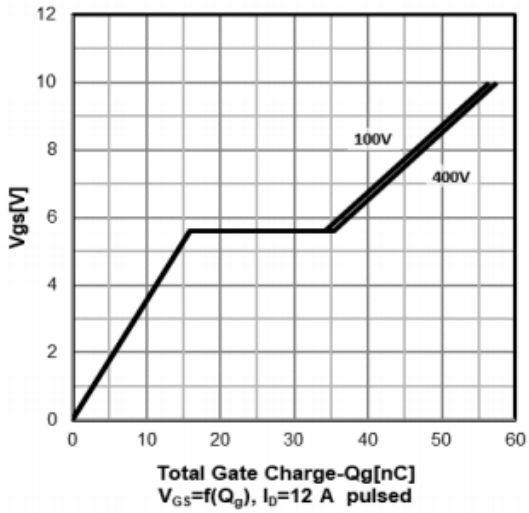
On resistance vs temperature



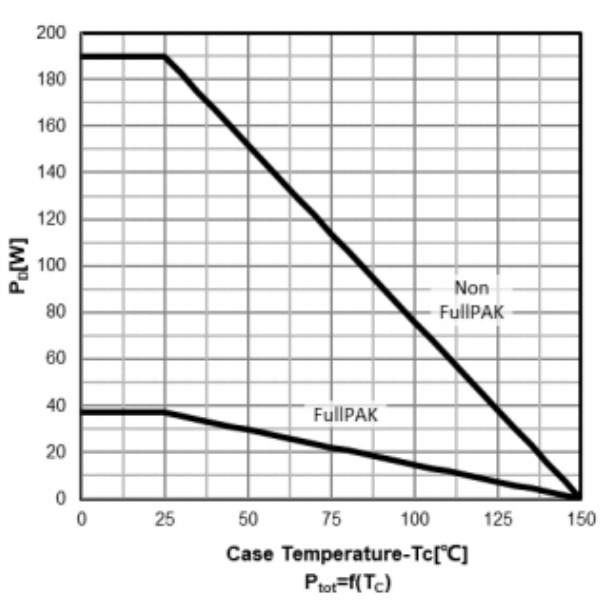
Typ. capacitances



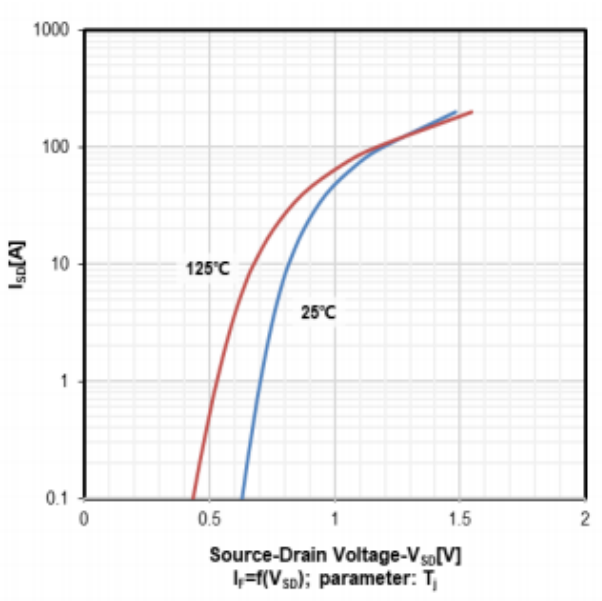
Typ. gate charge characteristics



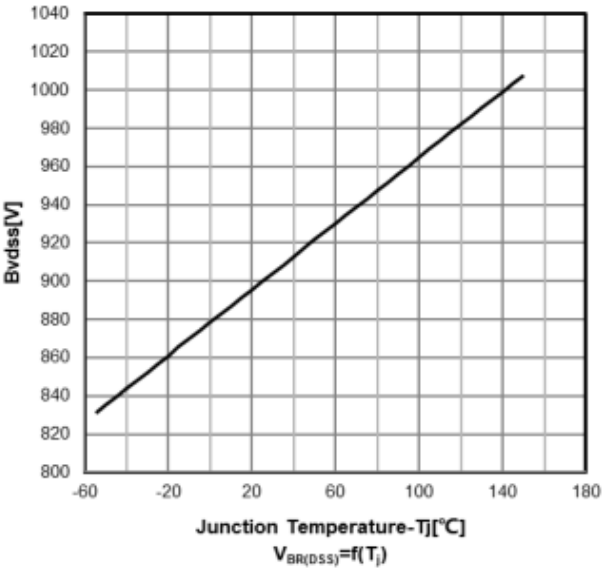
Power dissipation



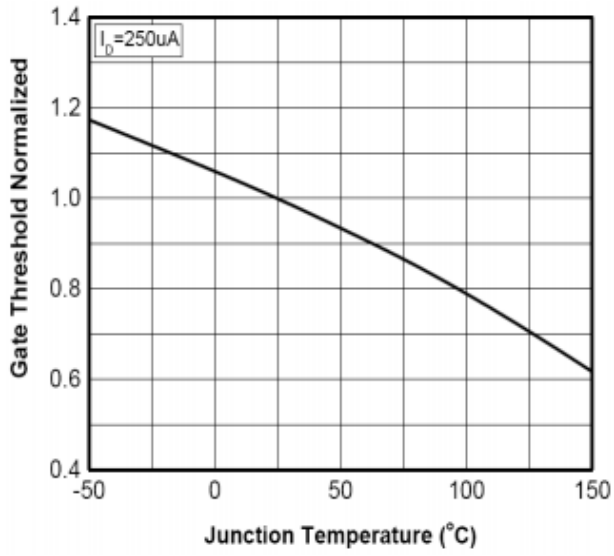
Forward characteristics of reverse diode



Drain-source breakdown voltage



Normalized $V_{GS(th)}$ characteristics



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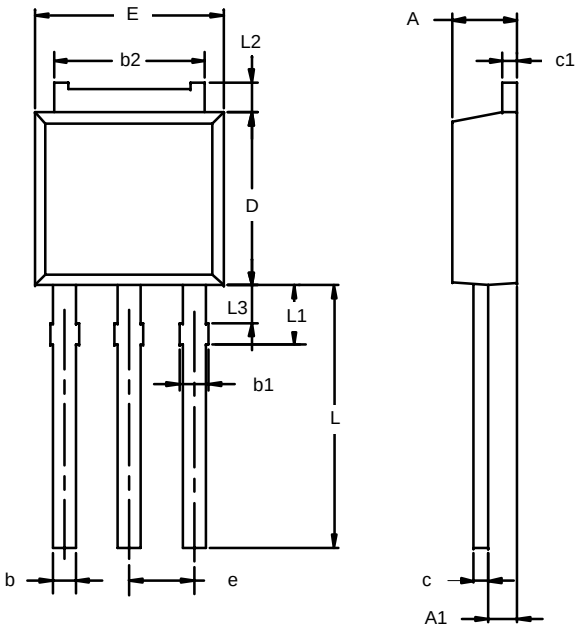

Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	2.21	2.38	0.087	0.094
A1	0.89	1.14	0.035	0.045
b	0.71	0.89	0.028	0.035
b1	0.76	1.14	0.030	0.045
b2	5.23	5.43	0.206	0.214
c	0.46	0.58	0.018	0.023
c1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
E	6.48	6.73	0.255	0.265
e	2.28 BSC		0.090 BSC	
L	8.89	9.53	0.350	0.375
L1	1.91	2.28	0.075	0.090
L2	0.89	1.27	0.035	0.050
L3	1.15	1.52	0.045	0.060

Note: Dimension L3 is for reference only.

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